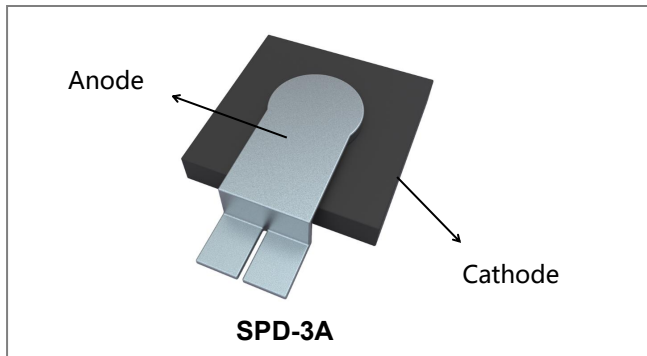


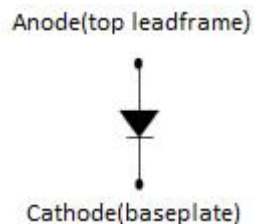
Power Surface Mount Schottky Rectifier (60V, 120Amp)



Features

- 175°C T_J operation
- Low forward voltage drop
- Low reverse leakage current
- High surge capacities
- High frequency operation
- Guaranteed reverse avalanche capability
- Low profile surface mount package
- Baseplate: Pure Sn plated; Terminals: Pure Sn plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Schematic & Pin Configuration



Applications

- Switching power supply
- Redundant power subsystems
- Reverse battery protection
- Converters
- Many other high current AC/DC power supplies

Maximum Ratings (limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _c =116°C, rectangular wave form	120	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	1650	A

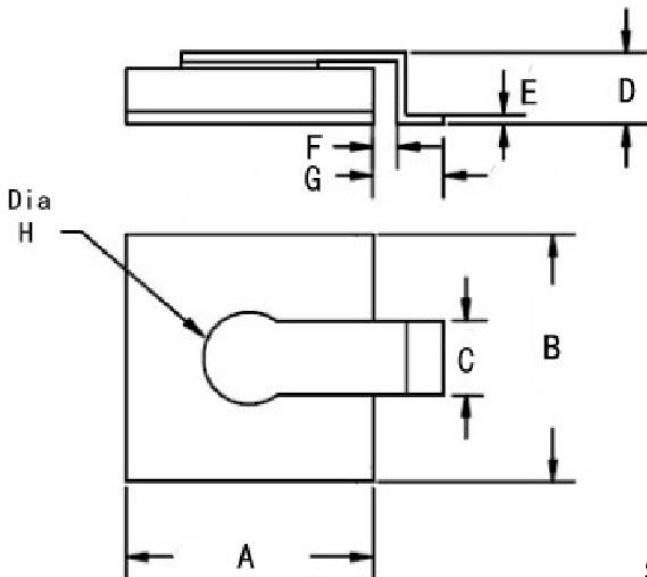
Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop *	V_{F1}	@ 5A, Pulse, $T_J = 25\text{ }^\circ\text{C}$ @ 10A, Pulse, $T_J = 25\text{ }^\circ\text{C}$ @ 120A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.45 0.49 0.73	0.50 0.54 0.76	V
	V_{F2}	@ 5A, Pulse, $T_J = 125\text{ }^\circ\text{C}$ @ 10A, Pulse, $T_J = 125\text{ }^\circ\text{C}$ @ 120A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.30 0.35 0.67	0.36 0.40 0.70	V
Reverse Current*	I_{R1}	@ $V_R = 15\text{V}$, Pulse, $T_J = 25\text{ }^\circ\text{C}$ @ $V_R = 60\text{V}$, Pulse, $T_J = 25\text{ }^\circ\text{C}$	3 20	20 100	μA
	I_{R2}	@ $V_R = 15\text{V}$, Pulse, $T_J = 125\text{ }^\circ\text{C}$ @ $V_R = 60\text{V}$, Pulse, $T_J = 125\text{ }^\circ\text{C}$	6 18	10 48	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	3400	4800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +175	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.20	$^\circ\text{C/W}$

Mechanical Dimensions (Inches/Millimeters)

SPD-3A

SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.08	11.78	0.436	0.464
B	11.08	11.78	0.436	0.464
C	4.93	5.23	0.194	0.206
D	2.57	3.37	0.101	0.133
E	0.20	0.60	0.008	0.024
F	1.02		0.040	
G	4.52		0.178	
H	5.59		0.220	

Suffix "R" Denotes Reversed Polarity

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

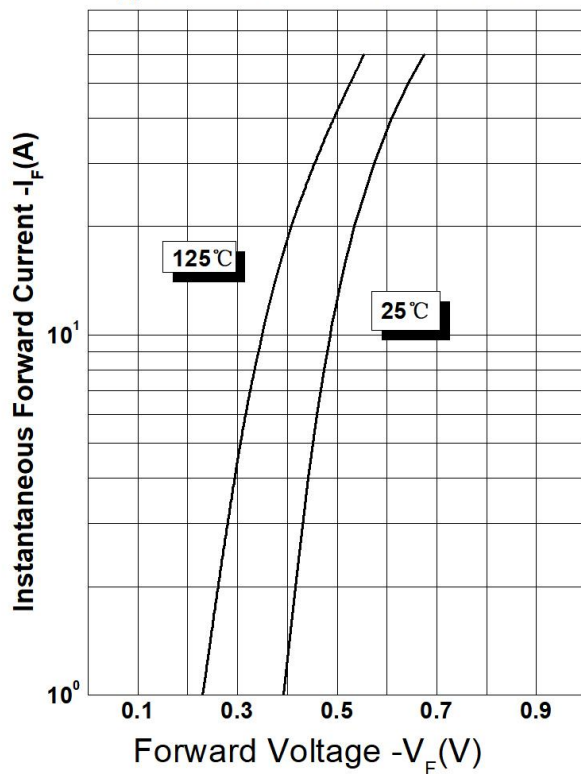


Figure 2
Typical Reverse Characteristics

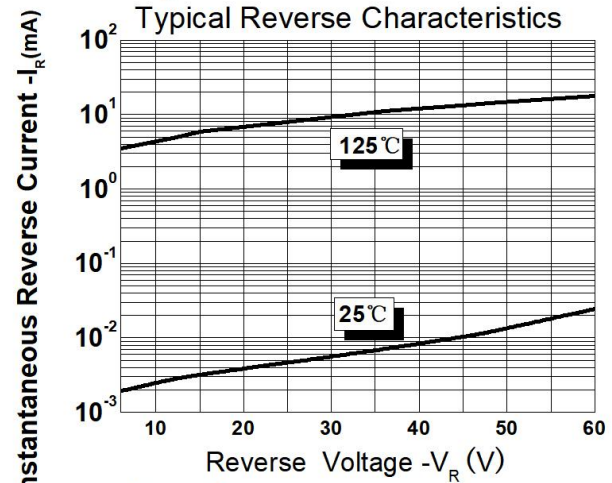
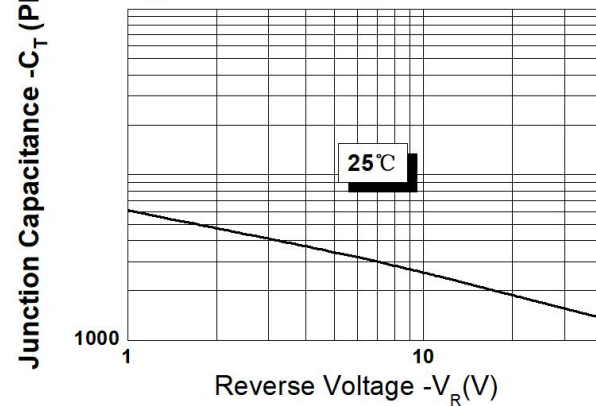


Figure 3
Typical Junction Capacitance



Ordering Information

Device	Package	Shipping
121SPC060A	SPD-3A(Pb-Free)	100pcs/ box



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